RAMA
UNIVERSITY

www.ramauniversity.ac.in

FACULTY OF ENGINEERING AND TECHNOLOGY

MEMS-035

Lecture -08

EPITAXY

This technology is quite similar to what happens in CVD processes, however, if the substrate is an ordered semiconductor crystal (i.e. silicon, gallium arsenide), it is possible with this process to continue building on the substrate with the same crystallographic orientation with the substrate acting as a seed for the deposition. If an amorphous/polycrystalline substrate surface is used, the film will also be amorphous or polycrystalline.

There are several technologies for creating the conditions inside a reactor needed to support epitaxial growth, of which the most important is **V**apor **P**hase **E**pitaxy (VPE). In this process, a number of gases are introduced in an induction heated reactor where only the substrate is heated. The temperature of the substrate typically must be at least 50% of the melting point of the material to be deposited.

An advantage of epitaxy is the high growth rate of material, which allows the formation of films with considerable thickness (>100µm). Epitaxy is a widely used technology for producing silicon on insulator (SOI) substrates. The technology is primarily used for deposition of silicon. A schematic diagram of a typical vapor phase epitaxial reactor is shown in the figure below

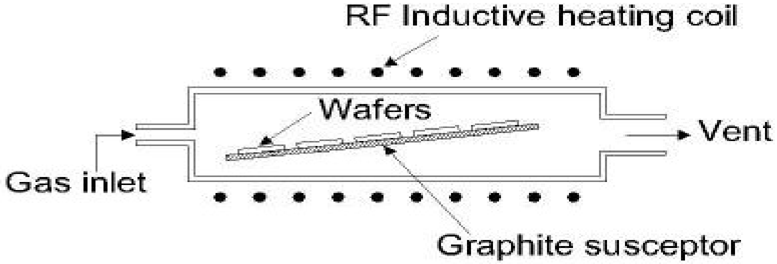

Figure 3: *Typical cold-wall vapor phase epitaxial reactor.*

ETCHING PROCESS

In order to form a functional MEMS structure on a substrate, it is necessary to etch the thin films previously deposited and/or the substrate itself. In general, there are two classes of etching processes:

1. Wet etching where the material is dissolved when immersed in a chemical solution
2. Dry etching where the material is sputtered or dissolved using reactive ions or a vapor phase etchant

WET ETCHING

This is the simplest etching technology. All it requires is a container with a liquid solution that will dissolve the material in question. Unfortunately, there are complications since usually a mask is desired to selectively etch the material. One must find a mask that will not dissolve or at least etches much slower than the material to be patterned. Secondly, some single crystal materials, such as silicon, exhibit anisotropic etching in certain chemicals. Anisotropic etching in contrast to isotropic etching means different etch rates in different directions in the material. The classic example of this is the <111> crystal plane sidewalls that appear when etching a hole in a <100> silicon wafer in a chemical such as potassium hydroxide (KOH). The principle of anisotropic and isotropic wet etching is illustrated in the figure below.

Wet etching works very well for etching thin films on substrates, and can also be used to etch the substrate itself. The problem with substrate etching is that isotropic processes will cause undercutting of the mask layer by the same distance as the etch depth. Anisotropic processes allow the etching to stop on certain crystal planes in the substrate.